BS EN 62416:2010

BSI Standards Publication

Semiconductor devices — Hot carrier test on MOS transistors

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The UK participation in its preparation was entrusted to Technical Committee EPL/47, Semiconductors.

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EUROPEAN STANDARD

NORME EUROPÉENNE

EUROPÄISCHE NORM

EN 62416

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English version

Semiconductor devices - Hot carrier test on MOS transistors
(IEC 62416:2010)

Dispositifs à semi-conducteurs - Essai de porteur chaud sur les transistors MOS
(CEI 62416:2010)

Halbleiterbauelemente - Hot-Carrier-Prüfverfahren für MOS-Transistoren
(IEC 62416:2010)

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CENELEC

European Committee for Electrotechnical Standardization
Comité Européen de Normalisation Electrotechnique
Europäisches Komitee für Elektrotechnische Normung

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Foreword

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The following dates were fixed:

– latest date by which the EN has to be implemented at national level by publication of an identical national standard or by endorsement	(dop)	2011-03-01
– latest date by which the national standards conflicting with the EN have to be withdrawn	(dow)	2013-06-01

Endorsement notice

The text of the International Standard IEC 62416:2010 was approved by CENELEC as a European Standard without any modification.

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